

## CORRECTION

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## Correction: Interface-engineered reliable HfO<sub>2</sub>-based RRAM for synaptic simulation

Qiang Wang,  <sup>a</sup> Gang Niu,  \*<sup>a</sup> Sourav Roy, <sup>a</sup> Yankun Wang, <sup>a</sup> Yijun Zhang, <sup>a</sup> Heping Wu, <sup>a</sup> Shijie Zhai, <sup>a</sup> Wei Bai, <sup>a</sup> Peng Shi, <sup>a</sup> Sannian Song, <sup>b</sup> Zhitang Song, <sup>b</sup> Ya-Hong Xie, <sup>c</sup> Zuo-Guang Ye,  <sup>d</sup> Christian Wenger, <sup>e</sup> Xiangjian Meng <sup>f</sup> and Wei Ren <sup>a</sup>

Correction for 'Interface-engineered reliable HfO<sub>2</sub>-based RRAM for synaptic simulation' by Qiang Wang *et al.*, *J. Mater. Chem. C*, 2019, DOI: 10.1039/c9tc04880d.

There was an error in the author list of this published article.

The corresponding authors for this paper are Gang Niu (gangniu@xjtu.edu.cn) and Wei Ren (wren@mail.xjtu.edu.cn). The footnote indicating that Qiang Wang and Gang Niu contributed equally to the work was not intended.

The corrected author list and notations are shown here.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

<sup>a</sup> Electronic Materials Research Laboratory, Key Laboratory of the Ministry of Education & International Center for Dielectric Research, School of Electronic Science and Engineering, Xi'an Jiaotong University, Xi'an 710049, China. E-mail: gangniu@xjtu.edu.cn, wren@mail.xjtu.edu.cn

<sup>b</sup> State Key Laboratory of Functional Materials for Informatics, Shanghai Institute of Microsystem and Information Technology, Chinese Academy of Sciences, 865 Changning Road, Shanghai 200050, China

<sup>c</sup> Department of Materials Science and Engineering, University of California, Los Angeles, California 90095, USA

<sup>d</sup> Department of Chemistry and 4D LABS, Simon Fraser University, Burnaby, British Columbia, V5A 1S6, Canada

<sup>e</sup> IHP-Leibniz-Institut für innovative Mikroelektronik, Im Technologiepark 25, 15236 Frankfurt (Oder), Germany

<sup>f</sup> National Laboratory for Infrared Physics, Shanghai Institute of Technical Physics, Chinese Academy of Sciences, Shanghai, 200083, China